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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/664,875	09/22/2003	Naoteru Matsubara	65933-044 4231	
7590 03/25/2005 McDERMOTT, WILL & EMERY 600 13th Street, N.W.			EXAMINER IM, JUNGHWA M	
			2811	,
			DATE MAILED: 03/25/2005	5

Please find below and/or attached an Office communication concerning this application or proceeding.

 	Application No.	Applicant(a)			
	Application No.	Applicant(s)			
	10/664,875	MATSUBARA ET AL.			
Office Action Summary	Examiner	Art Unit			
	Junghwa M. Im	2811			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply					
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on 07 Ja	anuary 2005.				
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims					
<u> </u>					
 4) Claim(s) 1-5 is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) Claim(s) is/are allowed. 6) Claim(s) 1-5 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or 					
Application Papers		·			
9) The specification is objected to by the Examine	r.				
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.					
Applicant may not request that any objection to the					
Replacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Ex	•				
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a)-(d) or (f).			
a) All b) Some * c) None of: 1. Certified copies of the priority documents					
2. Certified copies of the priority documents		ion No			
3. Copies of the certified copies of the prior					
application from the International Bureau	ı (PCT Rule 17.2(a)).				
* See the attached detailed Office action for a list of the certified copies not received.					
		_, _ ,			
Attachment(s)					
1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413)					
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)	Paper No(s)/Mail D 5) Notice of Informal F	ate Patent Application (PTO-152)			
Paper No(s)/Mail Date	6) Other:	·			

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DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's Admitted Prior Art (AAPA) in view of Gates et al. (US 6603204), hereinafter Gates.

Regarding claim 1, Fig. 1D of AAPA shows a semiconductor device comprising: a semiconductor substrate [2];

a multilayered film including a first dielectric film [2], an etching stopper [5] and a second dielectric film [6] stacked on said semiconductor substrate in this order; and

a via plug [1] and a metal interconnect [8B] formed in said multilayered film;

wherein the upper surface of said etching stopper is located under the upper surface level of said metal interconnect and the under surface of said etching stopper is located over the under surface level of said metal interconnect.

Fig. 1D of AAPA shows substantially the entire claimed structure except "the dielectric constant of said etching stopper being larger than that of said first and second dielectric films." Fig. 8 of Gates shows a semiconductor device with a multilayered film [52'] including a first dielectric film [54'], an etching stopper [56] and a second dielectric film [58'] stacked on said semiconductor substrate in this order, the dielectric constant of said etching stopper being larger than that of said first and second dielectric films (col. 4, lines 8-64).

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It would have been obvious to one of ordinary skill in the art at the time of the invention was made to incorporate the teachings of Gates into the device of AAPA in order to have the dielectric constant of the etching stopper being larger than that of the first and second dielectric films to enhance the circuit speed of the integrated circuit (col. 1, lines 1-10).

Regarding claim 2, Gates discloses the semiconductor device wherein the dielectric constant [k=1.1-5.5] of said etching stopper is less than or equal to 5 [col. 4, lines 60-65].

Regarding claims 3 and 4, Gates discloses the semiconductor device wherein the dielectric constant of said etching stopper is larger than or equal to a summation of 2 and the dielectric constant of either one of the dielectric constants [k=1.4-3.5] of said first and second dielectric films [col. 4, lines 15-17].

Regarding claim 5, Gates discloses said metal interconnect includes copper as a constituting element [col. 7, lines 34-36].

Response to Arguments

Applicant's arguments with respect to the pending claims have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth-in-37-CFR 1.136(a).

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A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Junghwa M. Im whose telephone number is (571) 272-1655. The examiner can normally be reached on MON.-FRI. 8:30AM-5:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C Lee can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

jmi

SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTRAL 2800